DATA SHEET

PLB16012U
NPN microwave power transistor

Product specification
Supersedes data of November 1994

1997 Feb 18

Philips
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NPN microwave power transistor PLB16012U

FEATURES

- Input matching cell allows an easier design of circuits
- Diffused emitter ballasting resistors providing excellent current sharing and withstanding a high VSWR
- Interdigitated structure provides high emitter efficiency
- Gold metallization realizes very stable characteristics and excellent lifetime
- Multicell geometry gives good balance of dissipated power and low thermal resistance.

APPLICATIONS

Common base, class C, power amplifiers at 1.6 GHz. Also suitable for operation in the 1.4 to 1.8 GHz range.

DESCRIPTION

NPN silicon planar epitaxial microwave power transistor in a SOT437A glued cap metal ceramic flange package with base connected to flange.

QUICK REFERENCE DATA

Microwave performance up to T_{mb} = 25 °C in a common base class C narrowband amplifier.

MODE OF OPERATION	f (GHz)	V_{CC} (V)	P_L (W)	G_p (dB)	η_C (%)	Z_i; Z_L (Ω)
Class C (CW)	1.6	28	10	>8	>45	see Figs 5 and 6

PINNING - SOT437A

PIN	DESCRIPTION
1	collector
2	emitter
3	base connected to flange

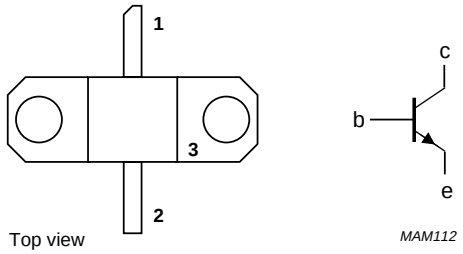


Fig.1 Simplified outline and symbol.

WARNING
Product and environmental safety - toxic materials
This product contains beryllium oxide. The product is entirely safe provided that the BeO slab is not damaged. All persons who handle, use or dispose of this product should be aware of its nature and of the necessary safety precautions. After use, dispose of as chemical or special waste according to the regulations applying at the location of the user. It must never be thrown out with the general or domestic waste.

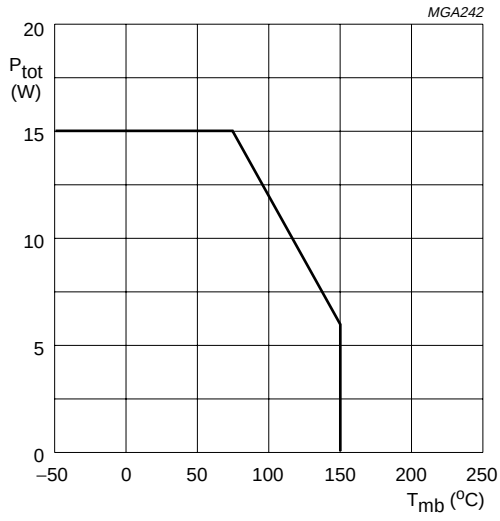
LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	45	V
V_{CEO}	collector-emitter voltage	open base	–	15	V
V_{CES}	collector-emitter voltage	R_{BE} = 0 Ω	–	40	V
V_{EBO}	emitter-base voltage	open collector	–	3	V
I_C	collector current (DC)		–	0.9	A
P_{tot}	total power dissipation	T_{mb} = 75 °C	–	15	W
T_{stg}	storage temperature		–65	+150	°C
T_j	operating junction temperature		–	200	°C
T_{sld}	soldering temperature	t ≤ 10 s; note 1	–	235	°C

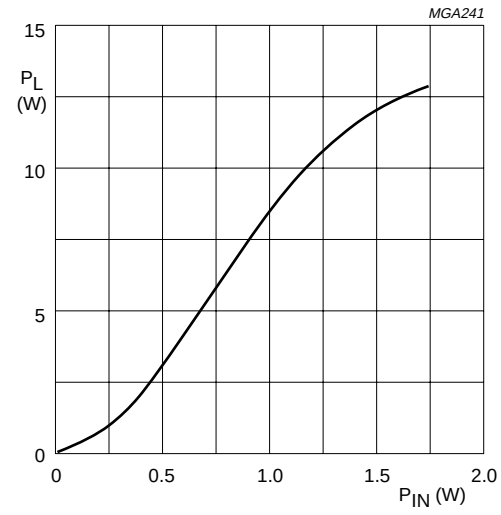
Note

1. Up to 0.3 mm from ceramic.



$P_{tot\ max}$ = 15 W.

Fig.2 Maximum power dissipation derating as a function of mounting base temperature.



V_{CC} = 28 V; f = 1.6 GHz.

Fig.3 Load power as a function of source power.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
$R_{th\ j\text{-}mb}$	thermal resistance from junction to mounting base	T_j = 100 °C	6	K/W
$R_{th\ mb\text{-}h}$	thermal resistance from mounting base to heatsink	note 1	0.3	K/W

Note

1. See *"Mounting recommendations in the General part of handbook SC19a".*

CHARACTERISTICS

T_{mb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
I_{CBO}	collector cut-off current	V_{CB} = 28 V; I_E = 0	0.3	mA
		V_{CB} = 35 V; I_E = 0	0.6	mA
I_{CES}	collector cut-off current	V_{CE} = 28 V; R_{BE} = 0 Ω	0.6	mA
I_{EBO}	emitter cut-off current	V_{EB} = 1.5 V; I_C = 0	25	μA

APPLICATION INFORMATION

Microwave performance up to T_{mb} = 25 °C in a common base test circuit as shown in Fig.4 and working in CW class C mode.

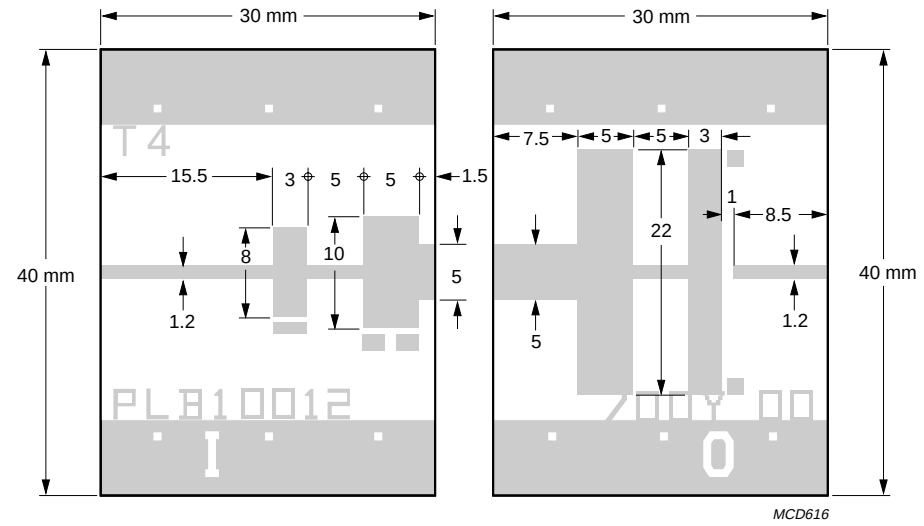
MODE OF OPERATION	f (GHz)	V_{CC} (V)	P_L (W)	G_p (dB)	η_C (%)	Z_i; Z_L (Ω)
Class C (CW) note 1	1.6	28	10	≥8 typ. 9.4	≥45 typ. 60	see Figs 5 and 6
Class C - 100 ms 50%	1.6	28	typ. 15	typ. 9.4	typ. 60	

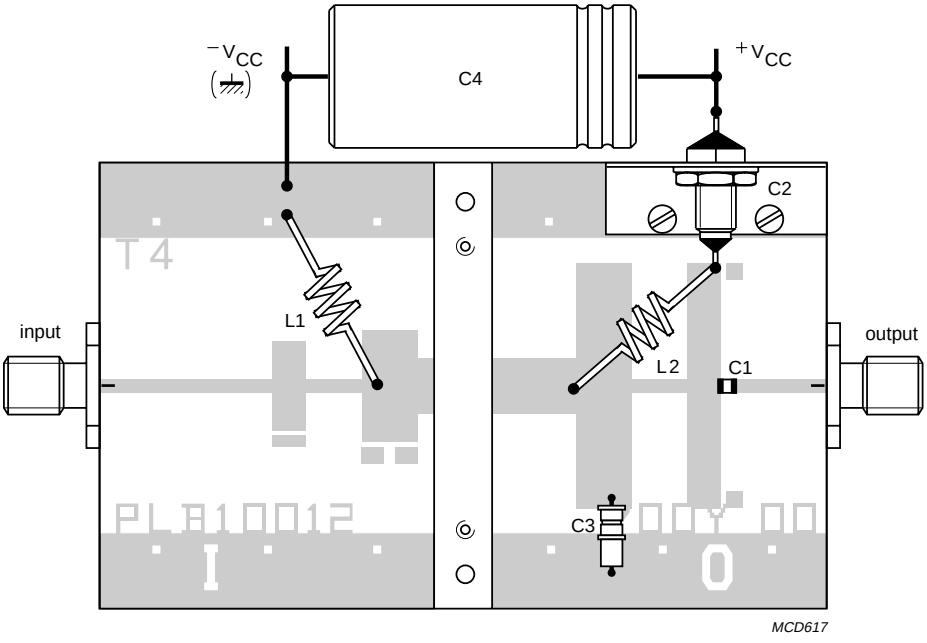
Note

1. May be used for narrowband or broadband amplifiers within the frequency range 1.4 to 1.8 GHz. Operation below 1.4 GHz may damage the transistor due to resonance of the internal output prematching circuit.

List of components (see Fig.4)

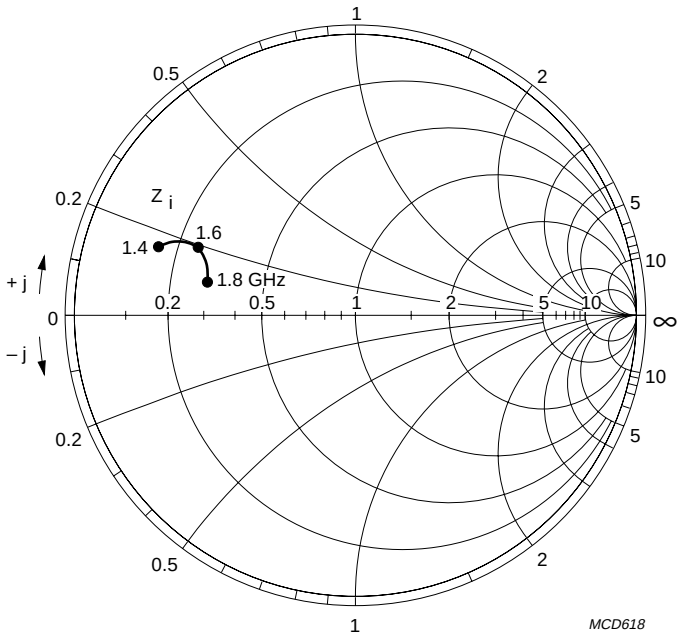
COMPONENT	DESCRIPTION	VALUE	DIMENSIONS	CATALOGUE NO.
L1, L2	5 turns 0.2 mm diameter copper wire		int. dia. = 2 mm	
C1	DC blocking capacitor	100 pF		
C2	feedthrough bypass capacitor			Erie, ref.1250-003
C3	trimmer capacitor	0.6 - 4.5 pF		AT-3-7-271SL
C4	electrolytic capacitor	150 μF, 45 V		





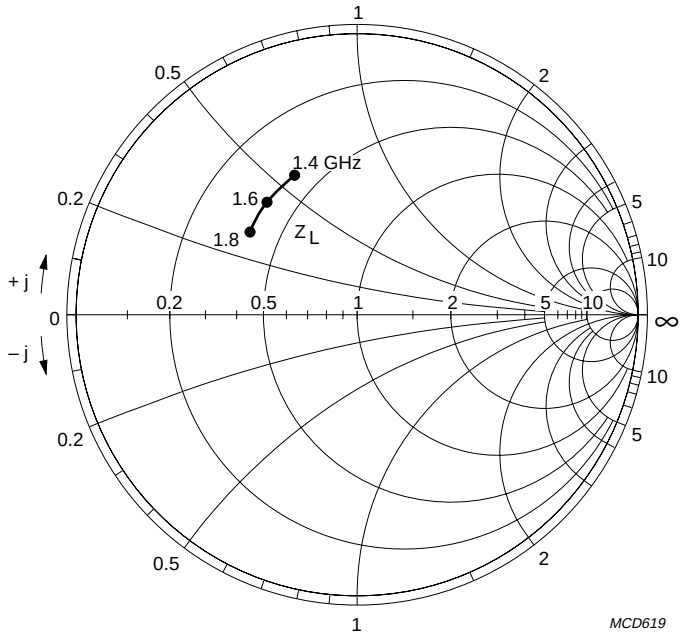
Substrate: Teflon fibre glass.
Thickness: 0.4 mm.
Permittivity: $\varepsilon_r = 2.55$.

Fig.4 Narrowband test circuit.



V_{CC} = 28 V; Z_o = 10 Ω.

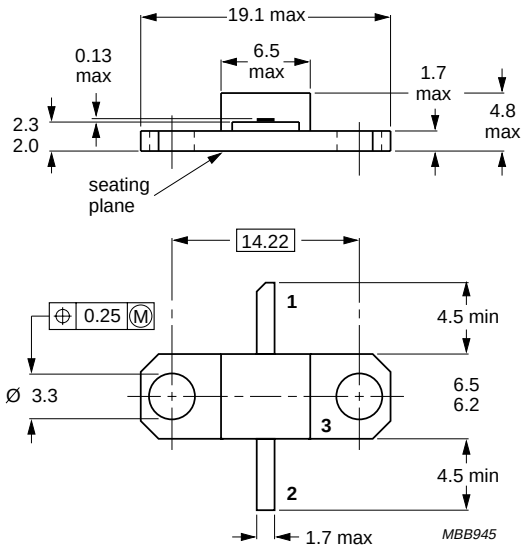
Fig.5 Input impedance as a function of frequency; typical values.



V_{CC} = 28 V; Z_o = 10 Ω.

Fig.6 Optimum load impedance as a function of frequency; typical values.

PACKAGE OUTLINE



Dimensions in mm.
Torque on nut: max 0.5 Nm.
Recommended screw: M3.
Recommended pitch for mounting screw: 19 mm.

Fig.7 SOT437A.

DEFINITIONS

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

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